

# Haizheng Song

## List of Publications by Year in descending order

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27  
papers

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docs citations

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times ranked

298  
citing authors

#	ARTICLE	IF	CITATIONS
1	4H-SiC homoepitaxy on nearly on-axis substrates using TFS-towards high quality epitaxial growth. Journal of Crystal Growth, 2016, 448, 97-104.	1.5	12
2	Study of Surface Morphology, Impurity Incorporation and Defect Generation during Homoepitaxial Growth of 4H-SiC Using Dichlorosilane. ECS Journal of Solid State Science and Technology, 2015, 4, P71-P76.	1.8	6
3	Interface Trap-Induced Nonideality in As-Deposited Ni/4H-SiC Schottky Barrier Diode. IEEE Transactions on Electron Devices, 2015, 62, 615-621.	3.0	33
4	Glide of threading edge dislocations after basal plane dislocation conversion during 4H-SiC epitaxial growth. Journal of Crystal Growth, 2015, 418, 7-14.	1.5	11
5	Large barrier, highly uniform and reproducible Ni-Si/4H-SiC forward Schottky diode characteristics: testing the limits of Tung's model. Journal Physics D: Applied Physics, 2014, 47, 295102.	2.8	21
6	Site Specific TEM Specimen Preparation for Characterization of Extended Defects in 4H-SiC Epilayers. Microscopy and Microanalysis, 2014, 20, 344-345.	0.4	0
7	Basal plane dislocation conversion near the epilayer/substrate interface in epitaxial growth of 4° off-axis 4H-SiC. Journal of Crystal Growth, 2013, 371, 94-101.	1.5	25
8	Trade-Off between Parasitic Deposition and SiC Homoepitaxial Growth Rate Using Halogenated Si-Precursors. ECS Journal of Solid State Science and Technology, 2013, 2, N3079-N3086.	1.8	5
9	Basal Plane Dislocation Mitigation in SiC Epitaxial Growth by Nondestructive Substrate Treatment. Crystal Growth and Design, 2012, 12, 1703-1707.	3.0	7
10	Investigations of defect evolution and basal plane dislocation elimination in CVD epitaxial growth of silicon carbide on eutectic etched epilayers. Journal of Crystal Growth, 2011, 320, 95-102.	1.5	16
11	Kinetic Analysis of InAsP by Metalorganic Vapor Phase Epitaxy Selective Area Growth Technique. Japanese Journal of Applied Physics, 2009, 48, 041102.	1.5	1
12	Non-linear surface reaction kinetics in GaAs selective area MOVPE. Journal of Crystal Growth, 2008, 310, 4731-4735.	1.5	2
13	Surface Reaction Kinetics of InP and InAs Metalorganic Vapor Phase Epitaxy Analyzed by Selective Area Growth Technique. Japanese Journal of Applied Physics, 2008, 47, 7788.	1.5	3
14	Nonlinear Kinetic Analysis of InP and InAs Metal Organic Vapor Phase Epitaxy by Selective Area Growth Technique. Japanese Journal of Applied Physics, 2008, 47, 8269-8274.	1.5	3
15	Nonlinear Kinetics of GaAs MOVPE Examined by Selective Area Growth Technique. Journal of the Electrochemical Society, 2007, 154, H91.	2.9	21
16	Impact of Atomistic Surface Structure on Macroscopic Surface Reaction Rate in MOVPE of GaAs. Electrochemical and Solid-State Letters, 2007, 10, H123.	2.2	1
17	Effects of Zn- and S-Doping on Kinetics of GaAs Selective Area MOVPE. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	1
18	Reactor-scale uniformity of selective-area performance in InGaAsP system. Journal of Crystal Growth, 2007, 298, 59-63.	1.5	2

#	ARTICLE	IF	CITATIONS
19	Non-linear kinetic analysis on GaAs selective area MOVPE combined with macro-scale analysis to extract major reaction mechanism. Journal of Crystal Growth, 2007, 298, 32-36.	1.5	9
20	Effect of Surface Misorientation on the Kinetics of GaAs MOVPE Examined Using Selective Area Growth. Electrochemical and Solid-State Letters, 2006, 9, G104.	2.2	15
21	Decomposition Behavior of M(DPM) <sub>n</sub> (DPM = 2,2,6,6-Tetramethyl-3,5-heptanedionato; n = 2, 3, 4). Journal of Physical Chemistry A, 2006, 110, 13479-13486.	2.5	26
22	Effect of group V partial pressure on the kinetics of selective area MOVPE for GaAs on (100) exact and misoriented substrate. Journal of Crystal Growth, 2006, 287, 664-667.	1.5	13
23	Deposition of Sm <sub>2</sub> O <sub>3</sub> doped CeO <sub>2</sub> thin films from Ce(DPM) <sub>4</sub> and Sm(DPM) <sub>3</sub> (DPM=2,2,6,6-tetramethyl-3,5-heptanedionato) by aerosol-assisted metal-organic chemical vapor deposition. Thin Solid Films, 2006, 510, 88-94.	1.8	13
24	Formation and Rate Processes of Y <sub>2</sub> O <sub>3</sub> Stabilized ZrO <sub>2</sub> Thin Films from Zr(DPM) <sub>4</sub> and Y(DPM) <sub>3</sub> by Cold-Wall Aerosol-Assisted MOCVD. Journal of the Electrochemical Society, 2005, 152, C498.	2.9	12
25	Synthesis and characterization of Sm(DPM) <sub>3</sub> used as precursor for MOCVD. Journal of Crystal Growth, 2004, 267, 256-262.	1.5	13
26	Synthesis and characterization of volatile metal <sup>II</sup> -diketonate chelates of M(DPM) <sub>n</sub> (M=Ce, Gd, Y, Zr, Th, U, Pu, Np, Am, Cm, Bk, Cf, Es, Fm, Md, No, Lr). Journal of Crystal Growth, 2004, 267, 256-262.	1.5	27
27	Deposition of Y <sub>2</sub> O <sub>3</sub> stabilized ZrO <sub>2</sub> thin films from Zr(DPM) <sub>4</sub> and Y(DPM) <sub>3</sub> by aerosol-assisted MOCVD. Materials Letters, 2003, 57, 3833-3838.	2.6	14